

4V Drive Nch MOSFET

RSH110N03

Structure

Silicon N-channel MOSFET

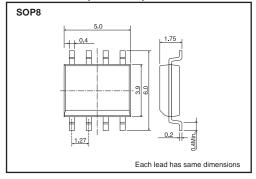
Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (SOP8).

Application

Power switching, DC / DC converter.

•Dimensions (Unit : mm)



Packaging specifications

Туре	Package	Taping
	Code	ТВ
	Basic ordering unit (pieces)	2500
RSH110N03	3	0

•Absolute maximum ratings (Ta=25°C)

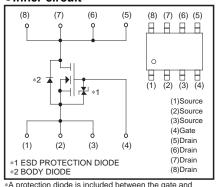
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Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	30	V
Gate-source voltage		Vgss	20	V
Drain autrent	Continuous	ID	±11	A
Drain current	Pulsed	IDP *1	±44	A
Source current	Continuous	ls	1.6	A
(Body diode)	Pulsed	Isp *1	22	A
Total power dissipation		P _D *2	2	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1% *2 Mounted on a ceramic board.

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	62.5	°C / W
* Mounted on a ceramic board.			

Inner circuit



A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

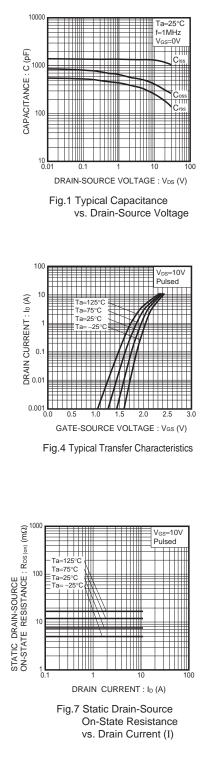
•Electrical characteristics (Ta=25°C)

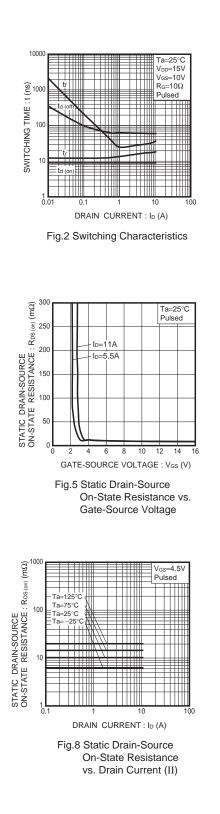
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	Igss	_	-	10	μA	Vgs=20V, Vds=0V	
Drain-source breakdown voltage	V(BR) DSS	30	-	-	V	I _D =1mA, V _{GS} =0V	
Zero gate voltage drain current	IDSS	-	-	1	μΑ	V _{DS} =30V, V _{GS} =0V	
Gate threshold voltage	VGS (th)	1.0	-	2.5	V	V _{DS} =10V, I _D =1mA	
Static drain-source on-starte resistance	RDS (on)	-	7.6	10.7		ID=11A, VGS=10V	
		-	10.3	14.5	mΩ	I _D =11A, V _{GS} =4.5V	
		-	11.2	15.7		I _D =11A, V _{GS} =4V	
Forward transfer admittance	Y _{fs} *	8.0	-	-	S	I _D =11A, V _{DS} =10V	
Input capacitance	Ciss	-	1300	-	рF	Vps=10V	
Output capacitance	Coss	-	410	-	рF	V _{GS} =0V	
Reverse transfer capacitance	Crss	-	250	-	pF	f=1MHz	
Turn-on delay time	t _{d (on)} *	_	9	-	ns	I _D =5.5A, V _{DD} ≒15V	
Rise time	tr *	-	17	-	ns	Vgs=10V	
Turn-off delay time	t _{d (off)} *	-	60	-	ns	R _L =2.73Ω	
Fall time	t _f *	-	30	-	ns	R _G =10Ω	
Total gate charge	Qg *	-	17	-	nC	V _{DD} ≒15V	
Gate-source charge	Q _{gs} *	_	3.3	-	nC	V _{GS} =5V	
Gate-drain charge	Q _{gd} *	_	7.1	_	nC	ID=11A	

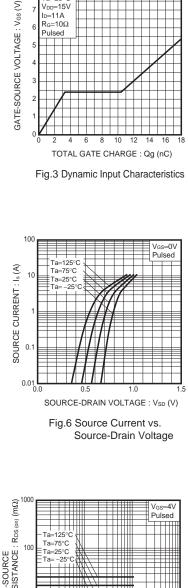
•Body diode characteristics (Source-Drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V _{SD} *	-	-	1.2	V	Is=6.4A, V _{GS} =0V

•Electrical characteristic curves







Ta=25°C

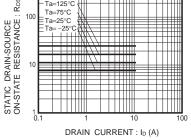


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current (III)

	Notes
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